



Integrated Device Technology, Inc.

**FAST CMOS 10-BIT
BUFFERS**

**IDT54/74FCT827AT/BT/CT/DT
IDT54/74FCT828AT/BT/CT**

T-52-07

FEATURES:

- Fastest CMOS logic family available
- A, B, C and D speed grades with 3.8ns tPD
- Available in DIP, SOIC, SSOP, CERPACK and LCC packages
- I_{OL} = 48mA (commercial), and 32mA (military)
- Clamp diodes on all inputs for ringing suppression
- CMOS power levels (1mW typ. static)
- True TTL input and output level compatible
- Substantially lower input current levels than AMD's bipolar Am29800 series (5µA max.)
- Product available in Radiation Tolerant and Radiation Enhanced versions
- Military product compliant to MIL-STD-883, Class B

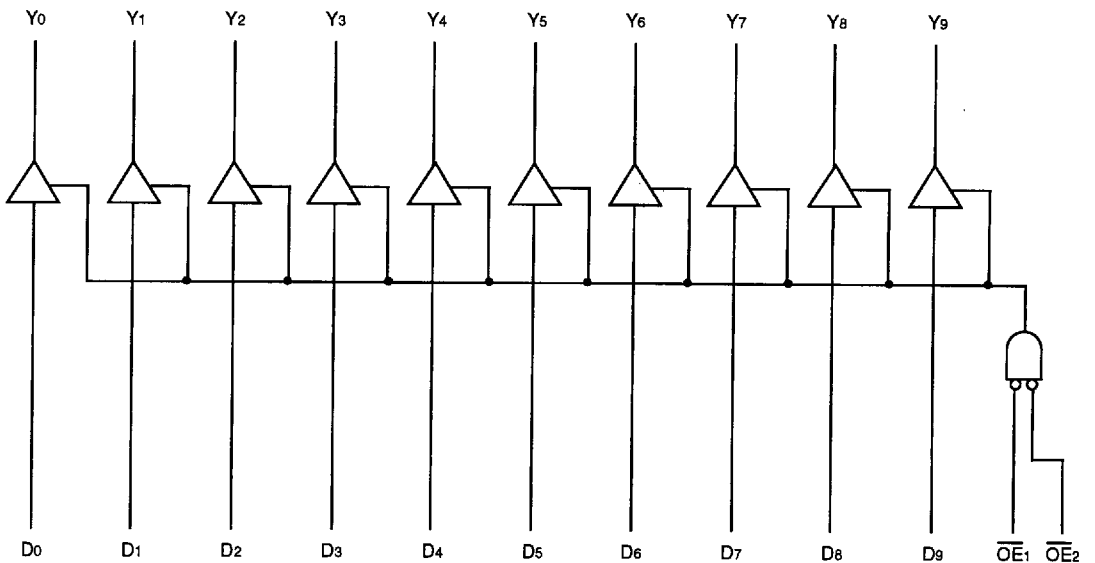
DESCRIPTION:

The IDT54/74FCT800 series is built using advanced CEMOS™, a dual metal CMOS technology.

The IDT54/74FCT827AT/BT/CT/DT and IDT54/74FCT828AT/BT/CT 10-bit bus drivers provide high-performance bus interface buffering for wide data/address paths or buses carrying parity. The 10-bit buffers have NAND-ed output enables for maximum control flexibility.

All of the IDT54/74FCT800 high-performance interface family are designed for high-capacitance load drive capability, while providing low-capacitance bus loading at both inputs and outputs. All inputs have clamp diodes and all outputs are designed for low-capacitance bus loading in high-impedance state.

FUNCTIONAL BLOCK DIAGRAM



PRODUCT SELECTOR GUIDE

10-Bit Buffer	
Non-inverting	IDT54/74FCT827AT/BT/CT/DT
Inverting	IDT54/74FCT828AT/BT/CT

CEMOS is a trademark of Integrated Device Technology, Inc.
FAST is a trademark of National Semiconductor Co.

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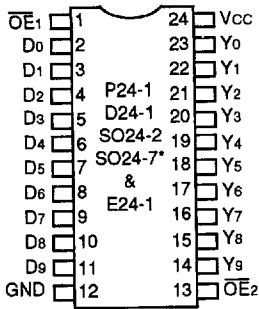
MILITARY AND COMMERCIAL TEMPERATURE RANGES

MAY 1992

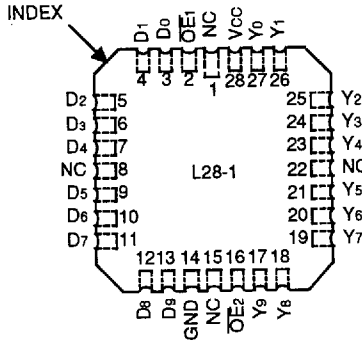
IDT54/74FCT827AT/BT/CT/DT, IDT54/74FCT828AT/BT/CT
HIGH-PERFORMANCE CMOS BUFFERS

MILITARY AND COMMERCIAL TEMPERATURE RANGES

PIN CONFIGURATIONS

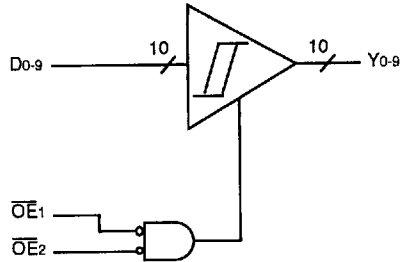


**DIP/SOIC/SSOP/CERPACK
TOP VIEW**



**LCC
TOP VIEW**

LOGIC SYMBOL



2573 cmv 02-04

* FCT827AT/BT/CT/DT only.

PIN DESCRIPTION

Names	I/O	Description
OE _i	I	When both are LOW the outputs are enabled. When either one or both are HIGH the outputs are High Z.
D _i	I	10-bit data input.
Y _i	O	10-bit data output.

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FUNCTION TABLES

IDT54/74FCT827T (NON-INVERTING)⁽¹⁾

Inputs			Output	Function
OE ₁	OE ₂	D _i	Y _i	
L	L	L	L	Transparent
L	L	H	H	
H	X	X	Z	Three-State
X	H	X	Z	

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IDT54/74FCT828T (INVERTING)⁽¹⁾

Inputs			Output	Function
OE ₁	OE ₂	D _i	Y _i	
L	L	L	H	Transparent
L	L	H	L	
H	X	X	Z	Three-State
X	H	X	Z	

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NOTE:
1. H = HIGH, L = LOW, X = Don't Care, Z = High Impedance

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ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Rating	Commercial	Military	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	V
VTERM ⁽³⁾	Terminal Voltage with Respect to GND	-0.5 to Vcc	-0.5 to Vcc	V
TA	Operating Temperature	0 to +70	-55 to +125	°C
TBIAS	Temperature Under Bias	-55 to +125	-65 to +135	°C
TSTG	Storage Temperature	-55 to +125	-65 to +150	°C
PT	Power Dissipation	0.5	0.5	W
IOUT	DC Output Current	120	120	mA

NOTES: 2573 tbl 05

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability. No terminal voltage may exceed Vcc by +0.5V unless otherwise noted.
- Input and Vcc terminals only.
- Outputs and I/O terminals only.

CAPACITANCE (TA = +25°C, f = 1.0MHz)

Symbol	Parameter ⁽¹⁾	Conditions	Typ.	Max.	Unit
CIN	Input Capacitance	VIN = 0V	6	10	pF
COUT	Output Capacitance	VOUT = 0V	8	12	pF

NOTE: 2573 tbl 06

- This parameter is measured at characterization but not tested.

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Following Conditions Apply Unless Otherwise Specified:

Commercial: TA = 0°C to +70°C, Vcc = 5.0V ± 5%; Military: TA = -55°C to +125°C, Vcc = 5.0V ± 10%

Symbol	Parameter	Test Conditions ⁽¹⁾	Min.	Typ. ⁽²⁾	Max.	Unit
VIH	Input HIGH Level	Guaranteed Logic HIGH Level	2.0	—	—	V
VIL	Input LOW Level	Guaranteed Logic LOW Level	—	—	0.8	V
IiH	Input HIGH Current	Vcc = Max. Vi = 2.7V	—	—	5	µA
IiL	Input LOW Current	Vcc = Max. Vi = 0.5V	—	—	-5	µA
IOZH	High Impedance Output Current	Vcc = Max. Vo = 2.7V	—	—	10	µA
IOZL		Vcc = Max. Vo = 0.5V	—	—	-10	µA
Ii	Input HIGH Current	Vcc = Max., Vi = Vcc (Max.)	—	—	20	µA
VIK	Clamp Diode Voltage	Vcc = Min., IN = -18mA	—	-0.7	-1.2	V
Ios	Short Circuit Current	Vcc = Max. ⁽³⁾ , VO = GND	-60	-120	-225	mA
VOH	Output HIGH Voltage	Vcc = Min. VIN = VIH or VIL IOH = -6mA MIL. IOH = -8mA COM'L.	2.4	3.3	—	V
		IOH = -12mA MIL. IOH = -15mA COM'L.	2.0	3.0	—	V
			—	—	—	V
VOL	Output LOW Voltage	Vcc = Min. VIN = VIH or VIL IOH = 32mA MIL. IOH = 48mA COM'L.	—	0.3	0.5	V
VH	Input Hysteresis	—	—	200	—	mV
Icc	Quiescent Power Supply Current	Vcc = Max. VIN = GND or Vcc	—	0.2	1.5	mA

NOTES: 2573 tbl 07

- For conditions shown as Max. or Min., use appropriate value specified under Electrical Characteristics for the applicable device type.
- Typical values are at Vcc = 5.0V, +25°C ambient and maximum loading.
- Not more than one output should be shorted at one time. Duration of the short circuit test should not exceed one second.

IDT54/74FCT827AT/BT/CT/DT, IDT54/74FCT828AT/BT/CT
HIGH-PERFORMANCE CMOS BUFFERS

MILITARY AND COMMERCIAL TEMPERATURE RANGES

POWER SUPPLY CHARACTERISTICS

Symbol	Parameter	Test Conditions ⁽¹⁾		Min.	Typ. ⁽²⁾	Max.	Unit
ΔI_{CC}	Quiescent Power Supply Current TTL Inputs HIGH	$V_{CC} = \text{Max.}$ $V_{IN} = 3.4V^{(3)}$		—	0.5	2.0	mA
I_{CCD}	Dynamic Power Supply Current ⁽⁴⁾	$V_{CC} = \text{Max.}$ Outputs Open $\overline{OE}_1 = \overline{OE}_2 = \text{GND}$ One Input Toggling 50% Duty Cycle	$V_{IN} = V_{CC}$ $V_{IN} = \text{GND}$	—	0.15	0.25	mA/ MHz
I_C	Total Power Supply Current ⁽⁶⁾	$V_{CC} = \text{Max.}$ Outputs Open $f_i = 10\text{MHz}$ 50% Duty Cycle $\overline{OE}_1 = \overline{OE}_2 = \text{GND}$ One Bit Toggling	$V_{IN} = V_{CC}$ $V_{IN} = \text{GND}$	—	1.7	4.0	mA
			$V_{IN} = 3.4V$ $V_{IN} = \text{GND}$	—	2.0	5.0	
		$V_{CC} = \text{Max.}$ Outputs Open $f_i = 2.5\text{MHz}$ 50% Duty Cycle $\overline{OE}_1 = \overline{OE}_2 = \text{GND}$ Eight Bits Toggling	$V_{IN} = V_{CC}$ $V_{IN} = \text{GND}$	—	3.2	6.5 ⁽⁵⁾	
			$V_{IN} = 3.4V$ $V_{IN} = \text{GND}$	—	5.2	14.5 ⁽⁵⁾	

NOTES: 2573 tbl 08

1. For conditions shown as Max. or Min., use appropriate value specified under Electrical Characteristics for the applicable device type.
2. Typical values are at $V_{CC} = 5.0V$, $+25^\circ\text{C}$ ambient.
3. Per TTL driven input ($V_{IN} = 3.4V$); all other inputs at V_{CC} or GND .
4. This parameter is not directly testable, but is derived for use in Total Power Supply calculations.
5. Values for these conditions are examples of the I_{CC} formula. These limits are guaranteed but not tested.
6. $I_C = I_{QUIESCENT} + I_{INPUTS} + I_{DYNAMIC}$
 $I_C = I_{CC} + \Delta I_{CC} \cdot D \cdot N_T + I_{CCD} (f_{CP}/2 + f_i N_i)$
 $I_{CC} = \text{Quiescent Current}$
 $\Delta I_{CC} = \text{Power Supply Current for a TTL High Input } (V_{IN} = 3.4V)$
 $D = \text{Duty Cycle for TTL Inputs High}$
 $N_T = \text{Number of TTL Inputs at } D$
 $I_{CCD} = \text{Dynamic Current Caused by an Input Transition Pair (HLH or LHL)}$
 $f_{CP} = \text{Clock Frequency for Register Devices (Zero for Non-Register Devices)}$
 $f_i = \text{Input Frequency}$
 $N_i = \text{Number of Inputs at } f_i$
 All currents are in milliamps and all frequencies are in megahertz.

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IDT54/74FCT827AT/BT/CT/DT, IDT54/74FCT828AT/BT/CT
HIGH-PERFORMANCE CMOS BUFFERS

MILITARY AND COMMERCIAL TEMPERATURE RANGES

SWITCHING CHARACTERISTICS OVER OPERATING RANGE

Symbol	Parameter	Conditions ⁽¹⁾	54/74FCT827AT/828AT				54/74FCT827BT/828BT				Unit
			Com'l.		MIL.		Com'l.		MIL.		
			Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	
tPLH tPHL	Propagation Delay Di to Yi IDT54/74FCT827T (Non-inverting)	CL = 50pF RL = 500Ω	1.5	8.0	1.5	9.0	1.5	5.0	1.5	6.5	ns
		CL = 300pF ⁽³⁾ RL = 500Ω	1.5	15.0	1.5	17.0	1.5	13.0	1.5	14.0	
tPLH tPHL	Propagation Delay Di to Yi IDT54/74FCT828T (Inverting)	CL = 50pF RL = 500Ω	1.5	9.0	1.5	10.0	1.5	5.5	1.5	6.5	ns
		CL = 300pF ⁽³⁾ RL = 500Ω	1.5	14.0	1.5	16.0	1.5	13.0	1.5	14.0	
tPZH tPZL	Output Enable Time OEi to Yi	CL = 50pF RL = 500Ω	1.5	12.0	1.5	13.0	1.5	8.0	1.5	9.0	ns
		CL = 300pF ⁽³⁾ RL = 500Ω	1.5	23.0	1.5	25.0	1.5	15.0	1.5	16.0	
tPHZ tPLZ	Output Disable Time OEi to Yi	CL = 5pF ⁽³⁾ RL = 500Ω	1.5	9.0	1.5	9.0	1.5	6.0	1.5	7.0	ns
		CL = 50pF RL = 500Ω	1.5	10.0	1.5	10.0	1.5	7.0	1.5	8.0	

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Symbol	Parameter	Conditions ⁽¹⁾	54/74FCT827CT/828CT				54/74FCT827DT				Unit
			Com'l.		MIL.		Com'l.		MIL.		
			Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	
tPLH tPHL	Propagation Delay Di to Yi IDT54/74FCT827T (Non-inverting)	CL = 50pF RL = 500Ω	1.5	4.4	1.5	5.0	1.5	3.8	—	—	ns
		CL = 300pF ⁽³⁾ RL = 500Ω	1.5	10.0	1.5	11.0	1.5	7.5	—	—	
tPLH tPHL	Propagation Delay Di to Yi IDT54/74FCT828T (Inverting)	CL = 50pF RL = 500Ω	1.5	4.4	1.5	5.0	—	—	—	—	ns
		CL = 300pF ⁽³⁾ RL = 500Ω	1.5	10.0	1.5	11.0	—	—	—	—	
tPZH tPZL	Output Enable Time OEi to Yi	CL = 50pF RL = 500Ω	1.5	7.0	1.5	8.0	1.5	5.0	—	—	ns
		CL = 300pF ⁽³⁾ RL = 500Ω	1.5	14.0	1.5	15.0	1.5	9.0	—	—	
tPHZ tPLZ	Output Disable Time OEi to Yi	CL = 5pF ⁽³⁾ RL = 500Ω	1.5	5.7	1.5	6.7	1.5	4.3	—	—	ns
		CL = 50pF RL = 500Ω	1.5	6.0	1.5	7.0	1.5	4.3	—	—	

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NOTES:

1. See test circuit and waveforms.
2. Minimum limits are guaranteed but not tested on Propagation Delays.
3. These conditions are guaranteed but not tested.